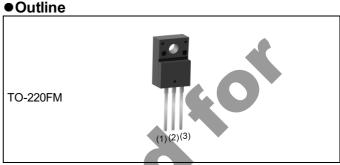
Nch 500V 9A Power MOSFET

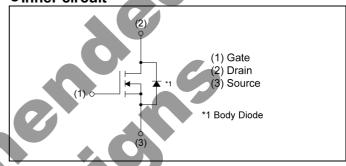
	7
V_{DSS}	500V
R _{DS(on)} (Max.)	0.72Ω
I _D	±9A
P_D	51W



Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 30V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

•Inner circuit



Packaging specifications

	Packing	Bulk
	Reel size (mm)	-
Tue	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	R5009ANX

Application

Switching

● **Absolute maximum ratings** (T_a = 25°C ,unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	500	V
Continuo a duoin ou mont	T _C = 25°C	I _D *1	±9	Α
Continuous drain current	T _C = 100°C	I _D *1	±4.3	А
Pulsed drain current		l _{DP} *2	±36	Α
Gate - Source voltage	V_{GSS}	±30	V	
Avalanche current, repetitive		l _{AR} *3	4.5	Α
Avalanche energy, single pulse		E _{AS} *3	5.4	mJ
Avalanche energy, repetitive		E _{AR} *5	3.5	mJ
Power dissipation (T _C = 25°C)	P _D *4	51	W	
Junction temperature	T _j	150	°C	
Operating junction and storage temp	T _{stg}	-55 ~ +150	°C	

● Absolute maximum ratings (T_a = 25°C)

Parameter	Symbol	Conditions	Values	Unit
Reverse diode dv/dt	dv/dt	-	15	V/ns
Drain - Source voltage slope	dv/dt	$V_{DS} = 400V, T_j = 125$ °C	50	V/ns

●Thermal resistance

Parameter	Symbol	Values			Unit
raidilletei	Symbol	Min.	Тур.	Max.	Uffil
Thermal resistance, junction - case	R _{thJC}		-	2.43	°C/W
Thermal resistance, junction - ambient	R _{thJA}		-	70	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-		265	°C

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions		Values		Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_D = 1mA$	500	ı	ı	V
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 500V, V_{GS} = 0V$ $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$		0.1	100 1000	μΑ
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = 10V, I _D = 1mA	2.5	ı	4.5	V
Static drain - source on - state resistance	R _{DS(on)} *6	$V_{GS} = 10V, I_D = 4.5A$ $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$	-	0.55 1.17	0.72	Ω
Gate resistance	R _G	f =1MHz, open drain	-	8.3	-	Ω

● Electrical characteristics (T_a = 25°C)

	0 1 1	O III		Values		11.7
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward Transfer Admittance	Y _{fs} *6	V _{DS} = 10V, I _D = 4.5A	2.5	-	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	650	•	
Output capacitance	C _{oss}	V _{DS} = 25V	-	400	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	30	-	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V	(7)	45.8	-	٦
Effective output capacitance, time related	C _{o(tr)}	V _{DS} = 0V to 400V	.	48.2	-	pF
Turn - on delay time	t _{d(on)} *6	V _{DD} ≈ 250V,V _{GS} = 10V	-	30	-	
Rise time	t _r *6	I _D = 4.5A	(-)	20	-	no
Turn - off delay time	t _{d(off)} *6	$R_L \approx 55.6\Omega$		62	-	ns
Fall time	t _f *6	$R_G = 10\Omega$	-	28	-	

● Gate charge characteristics (T_a = 25°C)

Darameter	Symbol Conditions	Values			1.1-:4	
Parameter		Min.	Тур.	Max.	Unit	
Total gate charge	Q_g^{*6}	V _{DD} ≃ 250V,	1	21	1	
Gate - Source charge	Q _{gs} *6	I _D = 9A,	-	5	-	nC
Gate - Drain charge	Q _{gd} *6	V _{GS} = 10V	-	9	-	
Gate plateau voltage	V _(plateau)	V _{DD} = 250V, I _D = 9A	-	6.0	-	V

^{*1} Limited only by maximum channel temperature allowed.

*6 Pulsed

^{*2} Pw \leq 10µs, Duty cycle \leq 1%

^{*3} L \doteqdot 500 μ H, V_{DD}=50V, R_G=25 Ω , STARTING T $_{j}$ =25 $^{\circ}$ C

^{*4} T_C=25°C

^{*5} L $\stackrel{.}{=}$ 500 μ H, V_{DD}=50V, R_G=25 Ω , STARTING T $_{j}$ =25 $^{\circ}$ C, f=10kHz

● Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Cumbal	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Continuous forward current	I _S *1	T - 25°C	-	-	9	А
Pulse forward current	I _{SP} *2	T _c = 25°C	-	-	36	А
Forward voltage	V _{SD} *6	$V_{GS} = 0V$, $I_S = 9A$	-	-	1.5	V
Reverse recovery time	t _{rr} *6		-	376	-	ns
Reverse recovery charge	Q _{rr} *6	I _S = 9A, V _{GS} =0V di/dt = 100A/µs		3.0	-	μC
Peak reverse recovery current	I _{mm} *6	α,, ατ 100, τμο		16	1	Α

● Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R _{th1}	0.263		C _{th1}	0.00166	
R _{th2}	0.977	K/W	C _{th2}	0.0191	Ws/K
R _{th3}	2.18		C _{th3}	0.46	

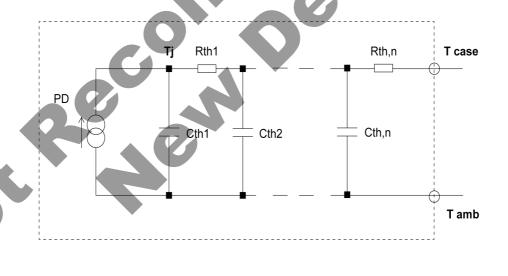


Fig.1 Power Dissipation Derating Curve

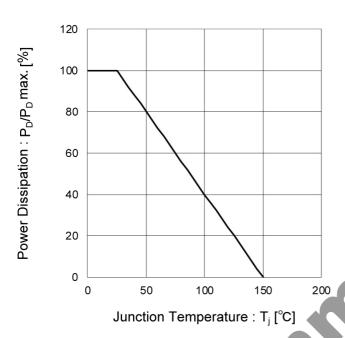


Fig.2 Maximum Safe Operating Area

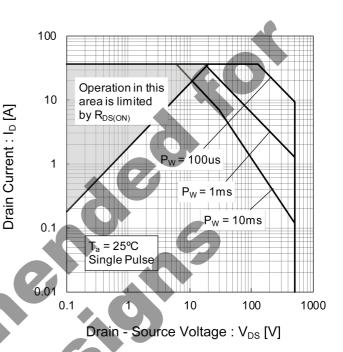


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

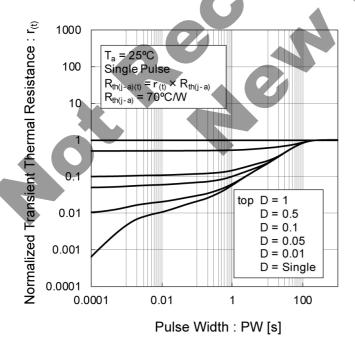


Fig.4 Avalanche Energy Derating Curve vs. Junction Temperature

Fig.5 Typical Output Characteristics(I)

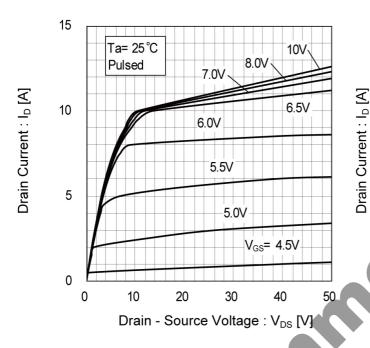


Fig.6 Typical Output Characteristics(II)

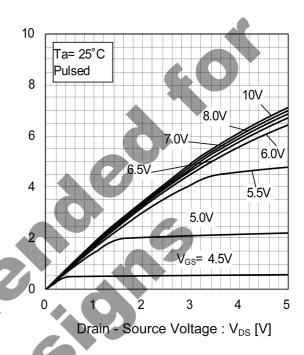


Fig.7 Tj = 150°C Typical Output
Characteristics (I)

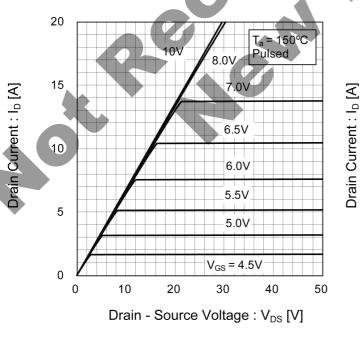


Fig.8 Tj = 150°C Typical Output Characteristics (II)

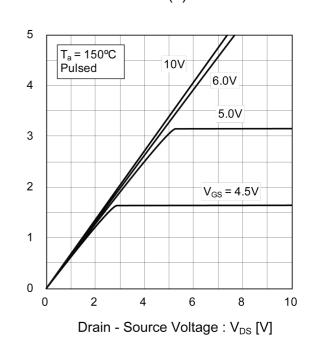


Fig.9 Breakdown Voltage vs.

Junction Temperature

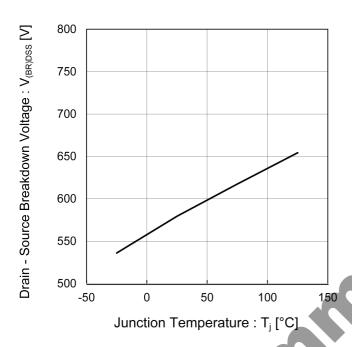


Fig.10 Typical Transfer Characteristics

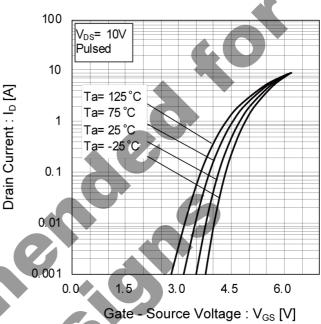


Fig.11 Gate Threshold Voltage vs. Junction Temperature

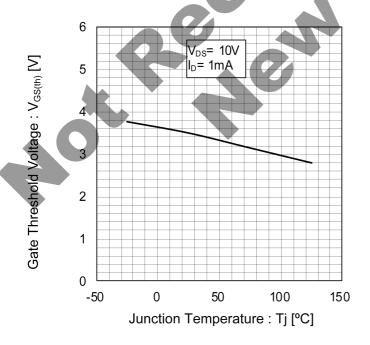


Fig.12 Forward Transfer Admittance vs.
Drain Current

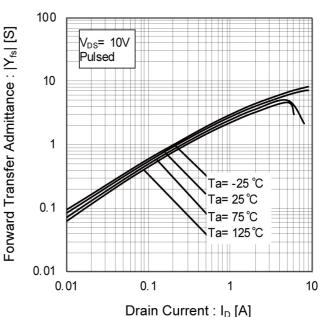
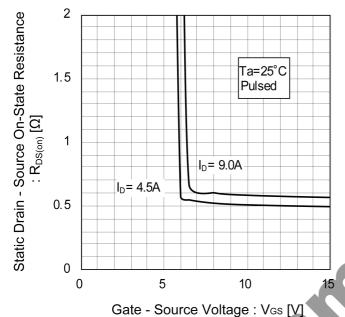


Fig.13 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Static Drain - Source On-State Resistance : R_{DS(on)} [Ω]

Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature

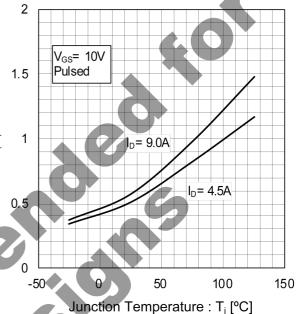


Fig.15 Static Drain - Source On - State
Resistance vs. Drain Current

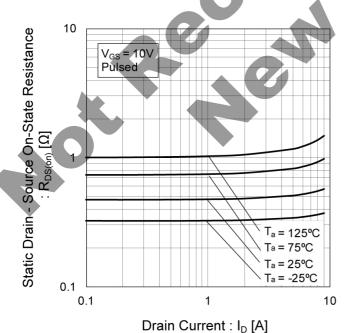


Fig.16 Typical Capacitance vs.
Drain - Source Voltage

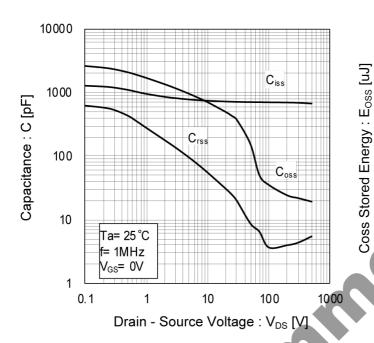


Fig.17 Coss Stored Energy

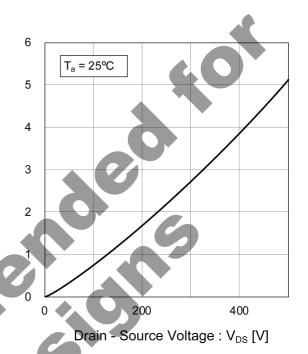


Fig.18 Switching Characteristics

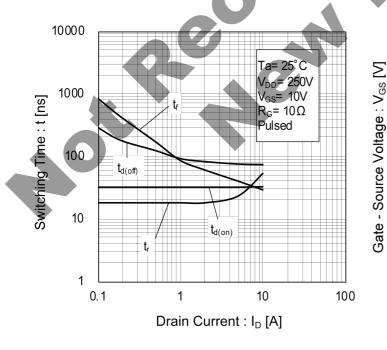


Fig.19 Dynamic Input Characteristics

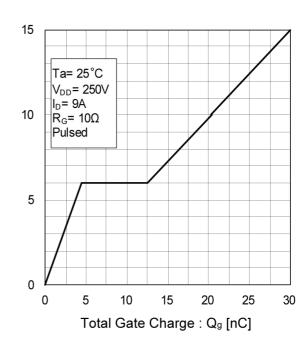
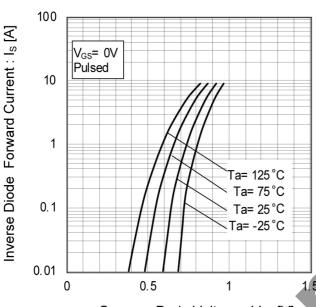
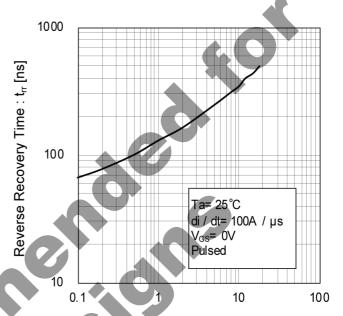


Fig.20 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V_{SD} [V]

Fig.21 Reverse Recovery Time vs.
Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]



Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

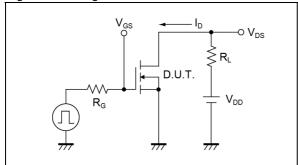


Fig.2-1 Gate Charge Measurement Circuit

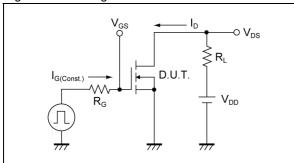


Fig.3-1 Avalanche Measurement Circuit

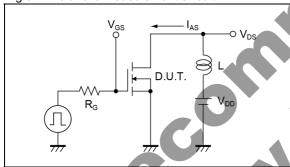


Fig.4-1 dv/dt Measurement Circuit

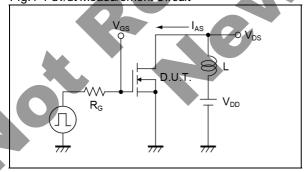


Fig.5-1 dv/dt Measurement Circuit

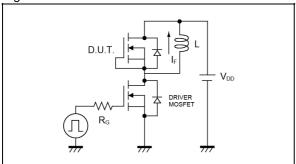


Fig.1-2 Switching Waveforms

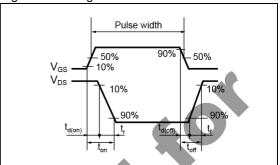


Fig.2-2 Gate Charge Waveform

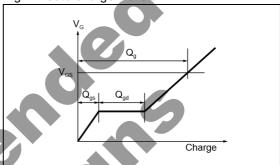


Fig.3-2 Avalanche Waveform

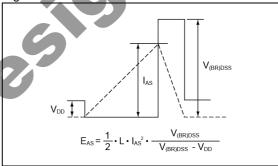


Fig.4-2 dv/dt Waveform

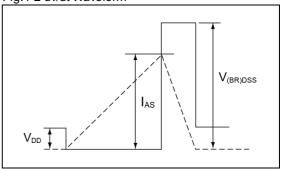
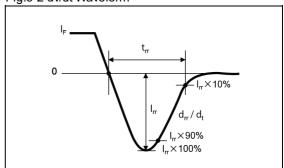
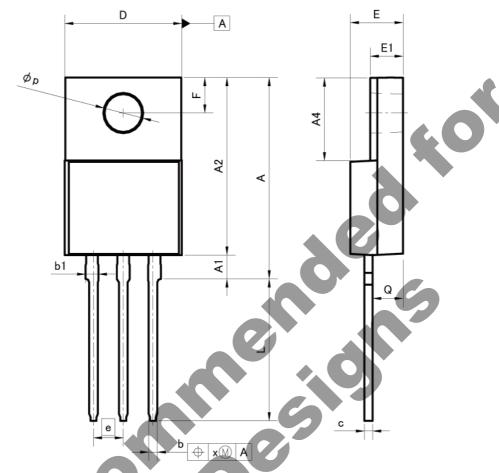


Fig.5-2 dv/dt Waveform



Dimensions





DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
A	16.60	17.60	0.654	0.693	
A1	1.80	2.20	0.071	0.087	
A2	14.80	15.40	0.583	0.606	
A4	6.80	7.20	0.268	0.283	
b	0.70	0.90	0.028	0.035	
b1	1.10	1.50	0.043	0.059	
С	0.70	0.85	0.028	0.033	
D	9.90	10.30	0.390	0.406	
E	4.40	4.80	0.173	0.189	
е	2.	54	0.100		
E1	2.70	3.00	0.106	0.118	
F	2.80	3.20	0.110	0.126	
L	11.50	12.50	0.453	0.492	
р	3.00	3.40	0.118	0.134	
Q	2.10	3.10	0.083	0.122	
х	-	0.38	_	0.015	

Dimension in mm/inches



Notice

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JAPAN	USA	EU	CHINA
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CLASSIV	CLASSⅢ	CLASSⅢ	CLASSII

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 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power, exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
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 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
 may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
 exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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